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restored

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Eiji Nishibe et al. Art Unit : Unknown
Serial No. : to be determined Examiner : Unknown
Filed : August 31, 2001
Title : SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

Commissioner for Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Prior to examination, please amend the application as follows:

In the abstract:

Insert the abstract after the last line on page 33.

~ A semiconductor device is provided with a gate electrode formed over a substrate that has gate oxide films disposed thereon. Source-drain regions of low and high concentration are formed next to the gate electrode. A diffusion region width of the source side of the source-drain regions is smaller than at least a diffusion region width of the drain side.~

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